**Product data sheet** 

# 1. General description

Planar passivated four quadrant triac in a SOT78 plastic package intended for use in bidirectional switching and phase control applications.

## 2. Features and benefits

- High blocking voltage capability
- Less sensitive gate for improved noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

# 3. Applications

- General purpose motor control
- General purpose switching

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	-	65	A
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 102 \text{ °C}$ ; Fig. 1; Fig. 2; Fig. 3	-	-	8	А
Static characte	eristics		,			,
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	5	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	11	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	30	70	mA





**4Q Triac** 

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2	<del>                                     </del>	Sym051
3	G	gate		·
mb	T2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BT137-800	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

**4Q Triac** 

# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 102$ °C; Fig. 1; Fig. 2; Fig. 3	-	8	А
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	65	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	71	Α
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	21	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T$ = 12 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2+ G+	-	50	A/µs
		$I_T$ = 12 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2+ G-	-	50	A/µs
		$I_T$ = 12 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2- G-	-	50	A/µs
		$I_T$ = 12 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2- G+	-	10	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_GM$	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

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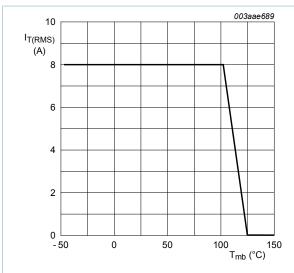


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

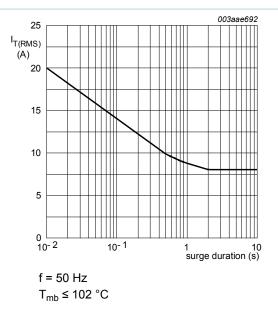
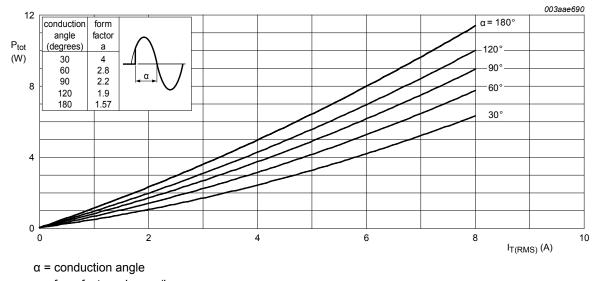


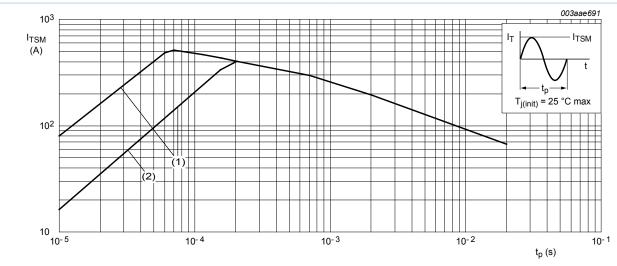
Fig. 2. RMS on-state current as a function of surge duration; maximum values



 $a = form factor = I_{T(RMS)}/I_{T(AV)}$ 

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

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 $t_p \le 20 \text{ ms}$ 

- (1) dI<sub>T</sub>/dt limit
- (2) T2- G+ quadrant limit

Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

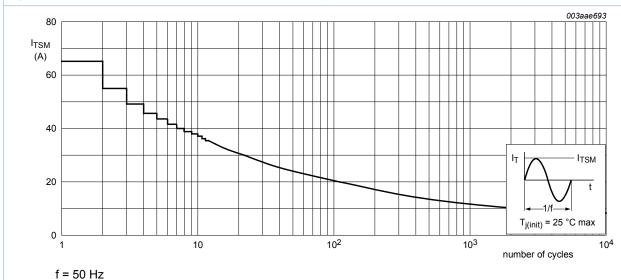


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	half cycle; Fig. 6	-	-	2.4	K/W
		full cycle; Fig. 6	-	-	2	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W

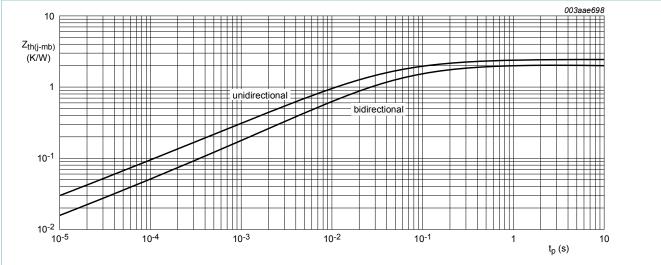


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

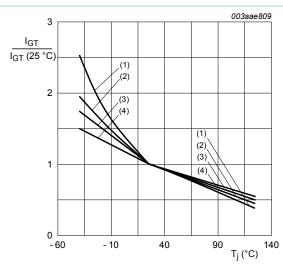
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# 9. Characteristics

Table 6 Characteristics

	Characteristics	Conditions	Min	True	May	I I m life
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara						
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	5	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } \underline{Fig. 7}$	-	8	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G-;}$ $T_j = 25 ^{\circ}\text{C; } \underline{\text{Fig. } 7}$	-	11	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	30	70	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	7	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 8$	-	16	45	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2\text{- G-;}$ $T_j = 25 \text{ °C; } \underline{Fig. 8}$	-	5	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	7	45	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	5	20	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics		1		1	
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	100	250	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 95 \text{ °C}; dI_{com}/dt = 3.6 \text{ A/}$ ms; $I_T = 8 \text{ A};$ gate open circuit	-	20	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 12 A; $V_D$ = 800 V; $I_G$ = 0.1 A; $dI_{G}/dt$ = 5 A/ $\mu$ s	-	2	-	μs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

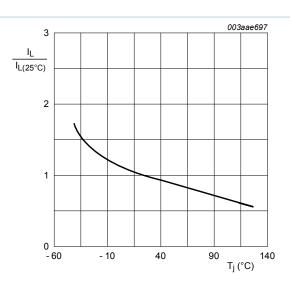


Fig. 8. Normalized latching current as a function of junction temperature

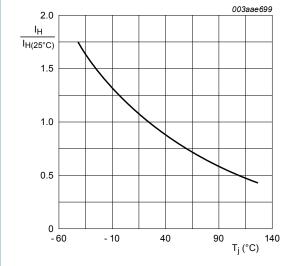
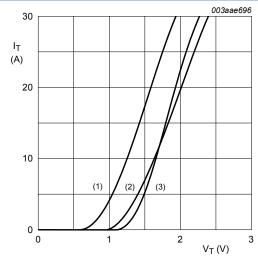


Fig. 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.264 \text{ V}$ 

 $R_s = 0.038 \Omega$ 

(1) T<sub>i</sub> = 125 °C; typical values

(2) T<sub>i</sub> = 125 °C; maximum values

(3)  $T_j = 25$  °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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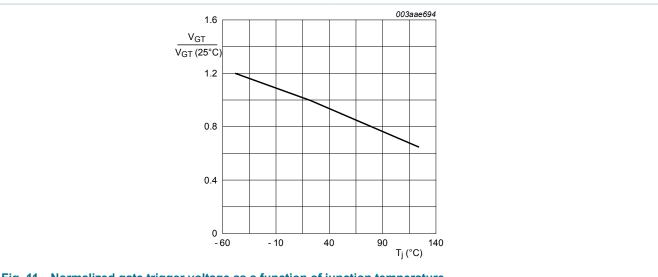
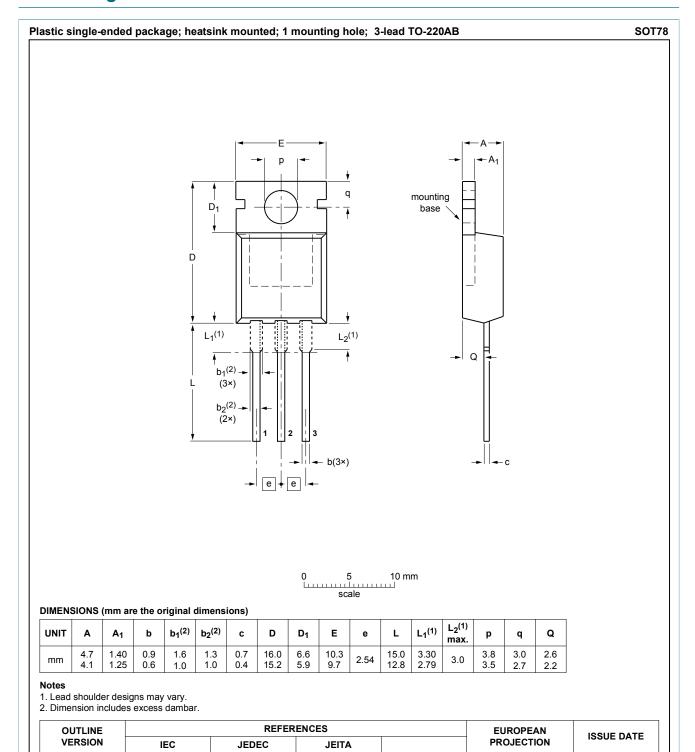


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

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# 10. Package outline



3-lead TO-220AB

Fig. 12. Package outline TO-220AB (SOT78)

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BT137-800

SOT78

SC-46

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